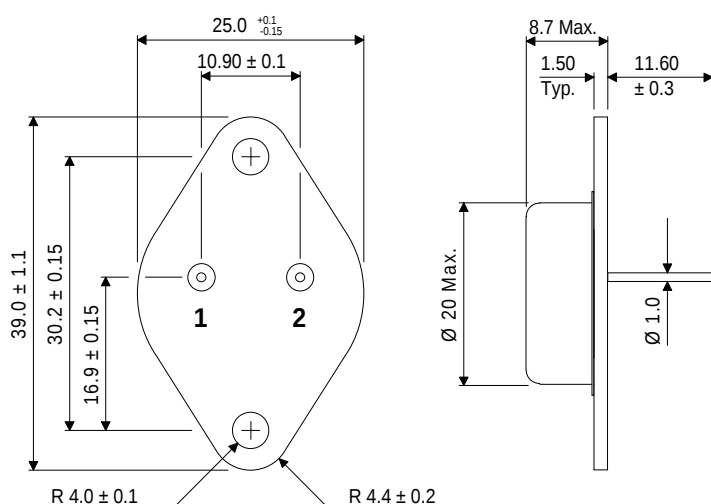


MECHANICAL DATA

Dimensions in mm

P-CHANNEL POWER MOSFET



TO-3

Pin 1 – Gate

Pin 2 – Drain

Case – Source

POWER MOSFETS FOR AUDIO APPLICATIONS

FEATURES

- HIGH SPEED SWITCHING
- P-CHANNEL POWER MOSFET
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (160V & 200V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODE
- N-CHANNEL ALSO AVAILABLE AS BUZ900 & BUZ901

ABSOLUTE MAXIMUM RATINGS

(T_{case} = 25°C unless otherwise stated)

		BUZ905	BUZ906
V _{DSX}	Drain – Source Voltage	-160V	-200V
V _{GSS}	Gate – Source Voltage	±14V	
I _D	Continuous Drain Current	-8A	
I _{D(PK)}	Body Drain Diode	-8A	
P _D	Total Power Dissipation @ T _{case} = 25°C	125W	
T _{stg}	Storage Temperature Range	-55 to 150°C	
T _j	Maximum Operating Junction Temperature	150°C	
R _{θJC}	Thermal Resistance Junction – Case	1.0°C/W	

STATIC CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
BV _{DSX} Drain – Source Breakdown Voltage	V _{GS} = 10V I _D = -10mA	BUZ905	-160			V
		BUZ906	-200			
BV _{GSS} Gate – Source Breakdown Voltage	V _{DS} = 0	I _G = ±100μA	±14			V
V _{GS(OFF)} Gate – Source Cut-Off Voltage	V _{DS} = -10V	I _D = -100mA	-0.15		-1.5	V
V _{DS(SAT)*} Drain – Source Saturation Voltage	V _{GD} = 0	I _D = -8A			-12	V
I _{DSX} Drain – Source Cut-Off Current	V _{GS} = -10V	V _{DS} = -160V BUZ905			-10	mA
		V _{DS} = -200V BUZ906			-10	
yfs* Forward Transfer Admittance	V _{DS} = -10V	I _D = -3A	0.7		2	S

DYNAMIC CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
C _{iss} Input Capacitance	V _{DS} = -10V f = 1MHz		734		pF
C _{oss} Output Capacitance			300		
C _{rss} Reverse Transfer Capacitance			26		
t _{on} Turn-on Time	V _{DS} = -20V I _D = -5A		120		ns
t _{off} Turn-off Time			60		

* Pulse Test: Pulse Width = 300μs , Duty Cycle ≤ 2%.

